

Photo Reflector

Model No. RFP-101X

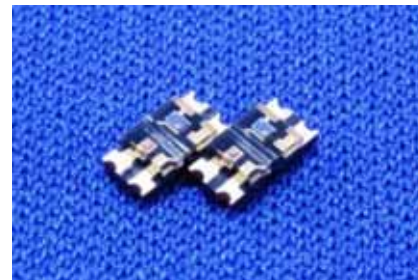
Photo reflector

RFP-101X offers microminiaturized surface mount type photo reflector, suitable as position detectors in tightly packed devices such as automatic devices etc.

Absolute Maximum Ratings

Ta = 25

Parameter		Symbol	Value	Unit
Emitter	DC forward current	I _F	50	mA
	DC Reverse Voltage	V _R	5	V
Detector	Collector-to-emitter Voltage	V _{CEO}	20	V
	Emitter-to-collector Voltage	V _{ECO}	5	V
	Collector power dissipation	P _C	60	V
Operating Temperature		Topr	-20 ~ +80	
Storage Temperature		Tstg	-30 ~ +90	



Electro-optical Characteristics

Ta = 25

Parameter		Symbol		Value	Unit	Condition
Emitter	Forward Voltage	V _F	Typ	2.1	V	I _F =10mA
	Reverse Current	I _R	Max	10	μA	V _R =5V
	Terminal Capacity	C _T	Typ	50	pF	V=0, f=1MHz
Detector	Dark Current	I _D	Max	200	nA	V _{CE} =10V
	Terminal Capacity	C _T	Typ	10	pF	V=0V, f=1MHz
Conversion Efficiency	Collector output current	I _C	Min	80	μA	V _{CE} =5V, I _F =10mA
			Max	2000		
Leakage current		I _{Leak}	Max	3.0	%	V _{CE} =5V, I _F =10mA
Collector-to-emitter saturation voltage		V _{CE(sat)}	Typ	0.5	V	I _F =20mA, I _C =0.1mA
Response	Rise Time	t _r	Typ	5	μs	V _{CE} =5V, I _C =1mA
	Fall Time	t _f	Typ	5		

External Dimension (unit: mm)

